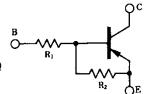


COMPOUND TRANSISTOR BN1A3Q

on-chip resistor PNP silicon epitaxial transistor For mid-speed switching

FEATURES

• On-chip bias resistor $(R_1 = 1.0 \; k\Omega, \; R_2 = 10 \; k\Omega)$



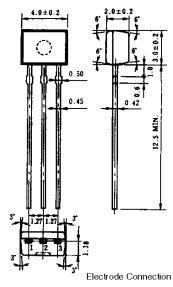
• Complementary transistor with BA1A3Q

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-60	V
Collector to emitter voltage	VCEO	–50	V
Emitter to base voltage	VEBO	-5	V
Collector current (DC)	Ic(DC)	-100	mA
Collector current (Pulse)	Ic(pulse) *	-200	mA
Total power dissipation	Рт	250	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

^{*} PW \leq 10 ms, duty cycle \leq 50 %

PACKAGE DRAWING (UNIT: mm)



- 1. Emitter
- 2. Collector
- 3. Base

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

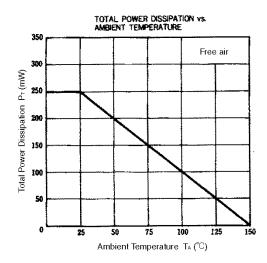
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -50 \text{ V}, I_E = 0$			-100	nA
DC current gain	h _{FE1} **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	35	60	80	_
DC current gain	hFE2 **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -50 \text{ mA}$	80	200		_
Collector saturation voltage	V _{CE(sat)} **	$I_C = -5.0 \text{ mA}, I_B = -0.25 \text{ mA}$		-0.04	-0.2	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ IB} = -100 \ \mu\text{A}$		-0.7	-0.5	V
High level input voltage	V _{IH} **	$V_{CE} = -0.2 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	-2.0	-1.0		V
Input resistance	R ₁		0.7	1.0	1.3	kΩ
E-to-B resistance	R ₂		7	10	13	kΩ
Turn-on time	ton	$Vcc = -5 \text{ V}, \text{ RL} = 1 \text{ k}\Omega$			0.2	μs
Storage time	t stg	$V_1 = -5 \text{ V}, \text{ PW} = 2 \mu \text{s}$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

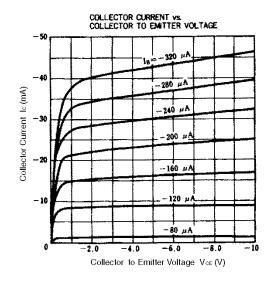
^{**} PW \leq 350 μ s, duty cycle \leq 2 %

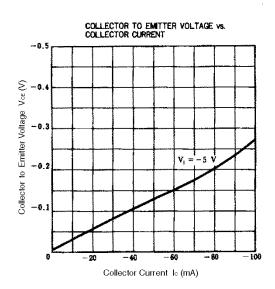
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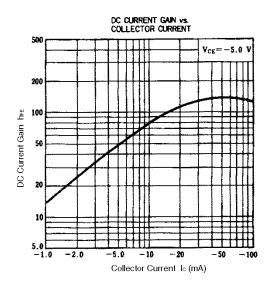


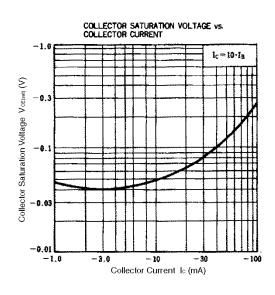
TYPICAL CHARACTERISTICS (Ta = 25°C)

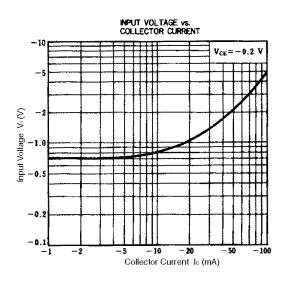


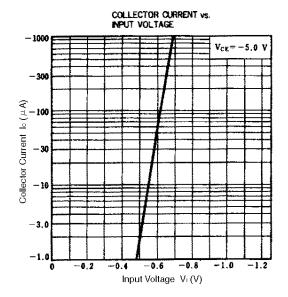


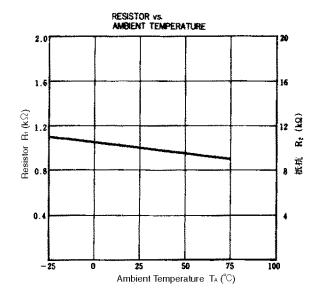












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